
Low Concentration Fluoride Chemistries For Cleaning Sub-0.25 Micron IC Devices

Semi-Aqueous Chemistry (SAC™)

US Patent 6,235,693; 6,248,704

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EKC Technology

- A Specialty Chemical Manufacturer
- Develops Efficient CMP and Cleaning Processes
- Manufacturers Novel CMP Products
 - Tungsten CMP Slurries
 - Copper, Oxide and Other Slurries
- Manufacturers Several Families of Removers
 - Aqueous HDA Chemistries
 - Water Rinsed SAC Chemistries

SAC™ Design Criteria

- Remove post etch residues @ 20°C to 30°C.
- Buffered chemistries with stable pH
- Low fluoride concentrations (<1 %)
- Designed for all types of cleaning equipment.
 - Spray tools: SEZ, FSI and SemiTool
 - Wet benches: Akrion and others
- Low viscosity for equipment and filter capability.
- Ability to remove post etch residues without attacking the silicon dioxide.

“Green Chemistries”

- Principles

- Look at potential hazards instead of exposure
- Economically driven not resource draining
- Minimum regulated content
- Use Problem Avoidance approach
- Life time impact considered at design stage



Green Chemistry Criteria

- Additional Criteria for material selection
 - Raw material should be environmentally friendly
 - Materials should be of reduced toxicity
 - Starting materials should be renewable
 - Starting material might be ‘waste’ from another process.

SAC™ Product Goals

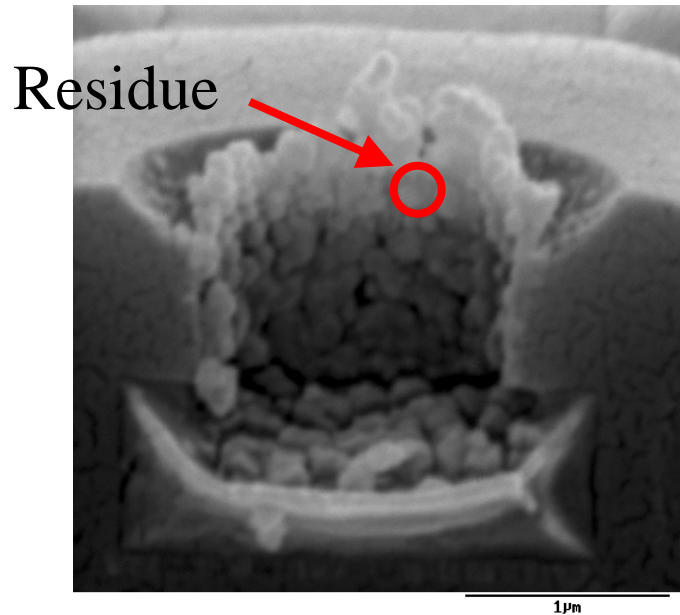
- Compatible with most low-k dielectric materials
- Minimum W-Plug corrosion
- Ability to remove surface mobile ions
- Non-hydroscopic formula
- Room temperature operation
- Water rinseable (no intermediate rinse required)
- Environmentally friendly products

SAC™ Physical Properties

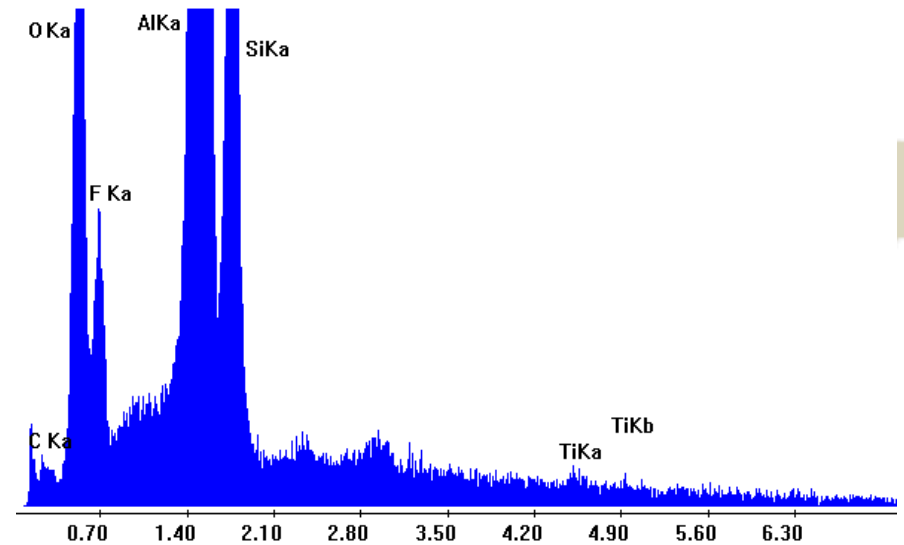
- pH: ~9
- Refractive Index: 1.41
- Viscosity: 1-2 cp
- Density: ~1
- Solubility in water: complete
- Physical state: liquid
- Appearance: clear
- Flash point: >110°C



Via Residue Samples*



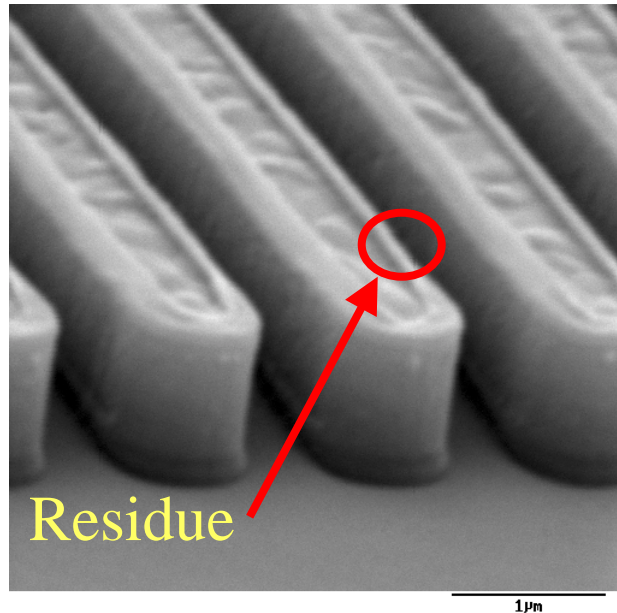
Oxide-SOG-TEOS via ($\text{\O}1.3 - 1.7\mu\text{m}$)
etched with Ar / CHF_3 / CF_4 chemistry
stopping on AlSiCu



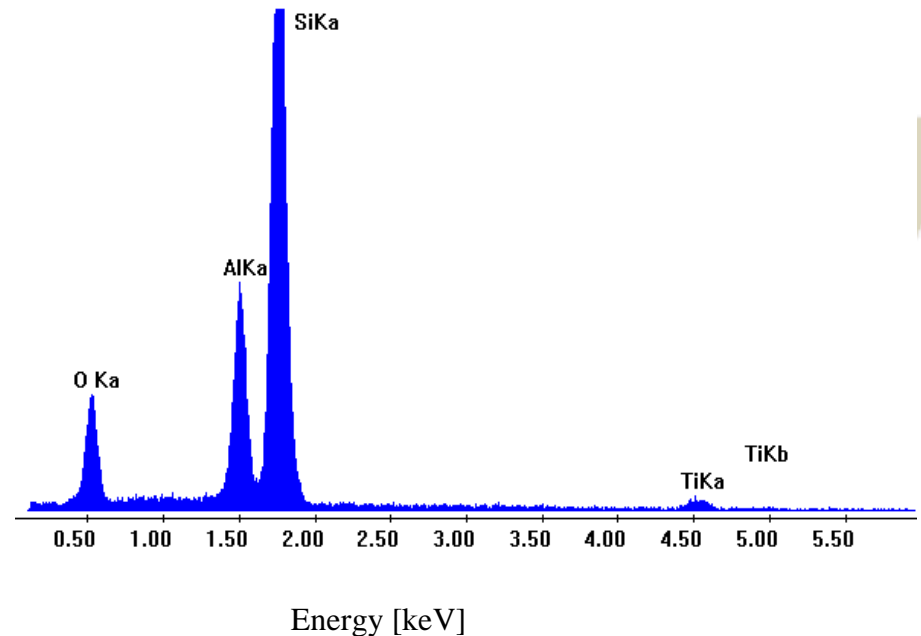
EDX spectrum of post-via-etch residue
("polymer veil")

* S. Lutter, Ph. D. Dissertation, Fachhochschule Regensburg, GR

Metal Residue Samples



0.8 μm Ti/TiN-AlSiCu-TiN lines (0.4 μm spacing) etched with $\text{Cl}_2 / \text{BCl}_3$ chemistry



EDX spectrum of post-metal-etch residue

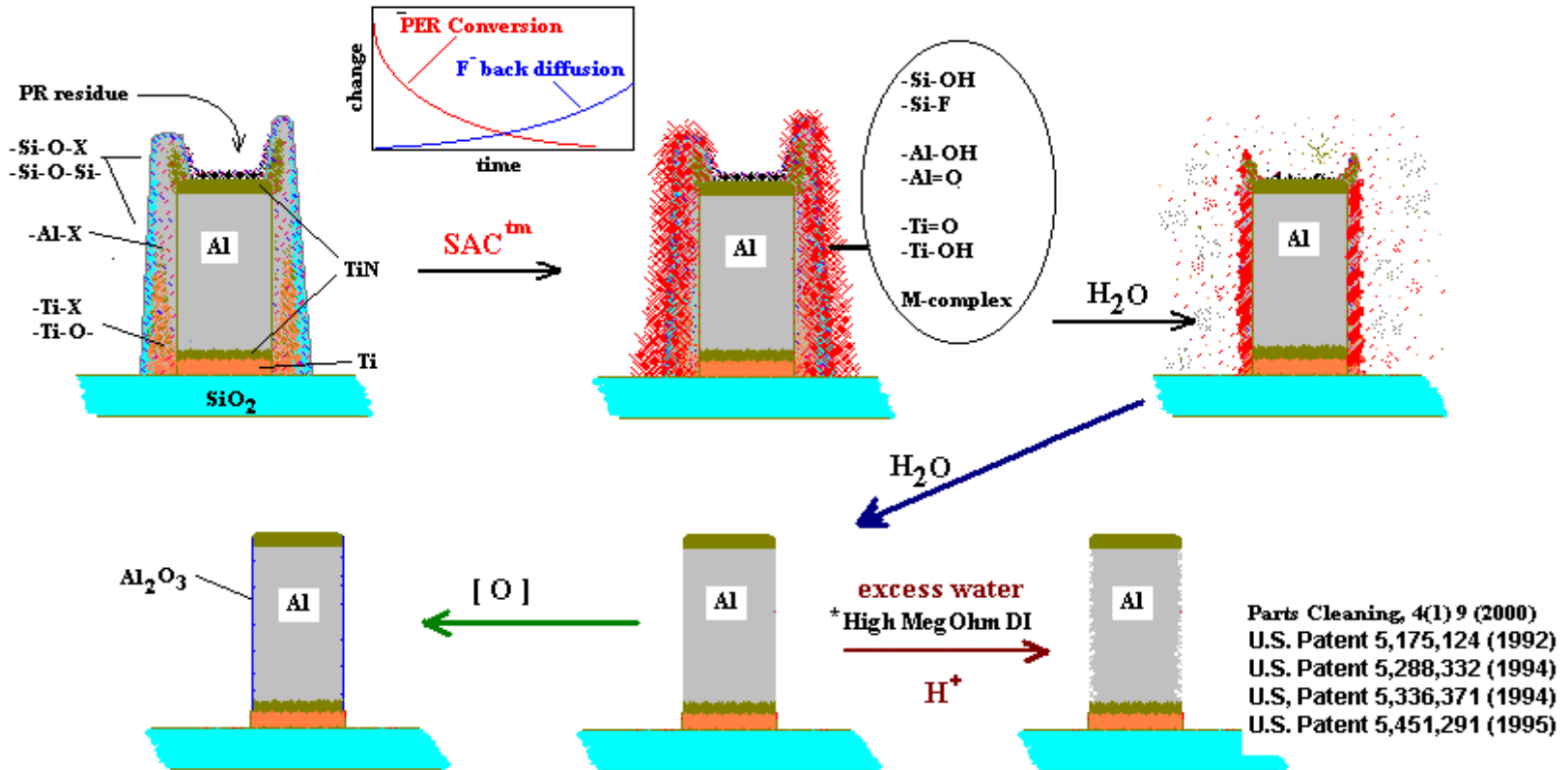
* S. Lutter, Ph. D. Dissertation, Fachhochschule Regensburg, GR

SAC™ Chemistries

- SAC™ chemistries use different principles for removing PER (post etch residue)
- The PER are not actively “etched” during the cleaning process as with HDA™ chemistries.
- The SAC™ chemistries are designed to use low concentrations of active fluoride species.
- The PER’s are converted to new reactive species with the SAC™ chemistries.

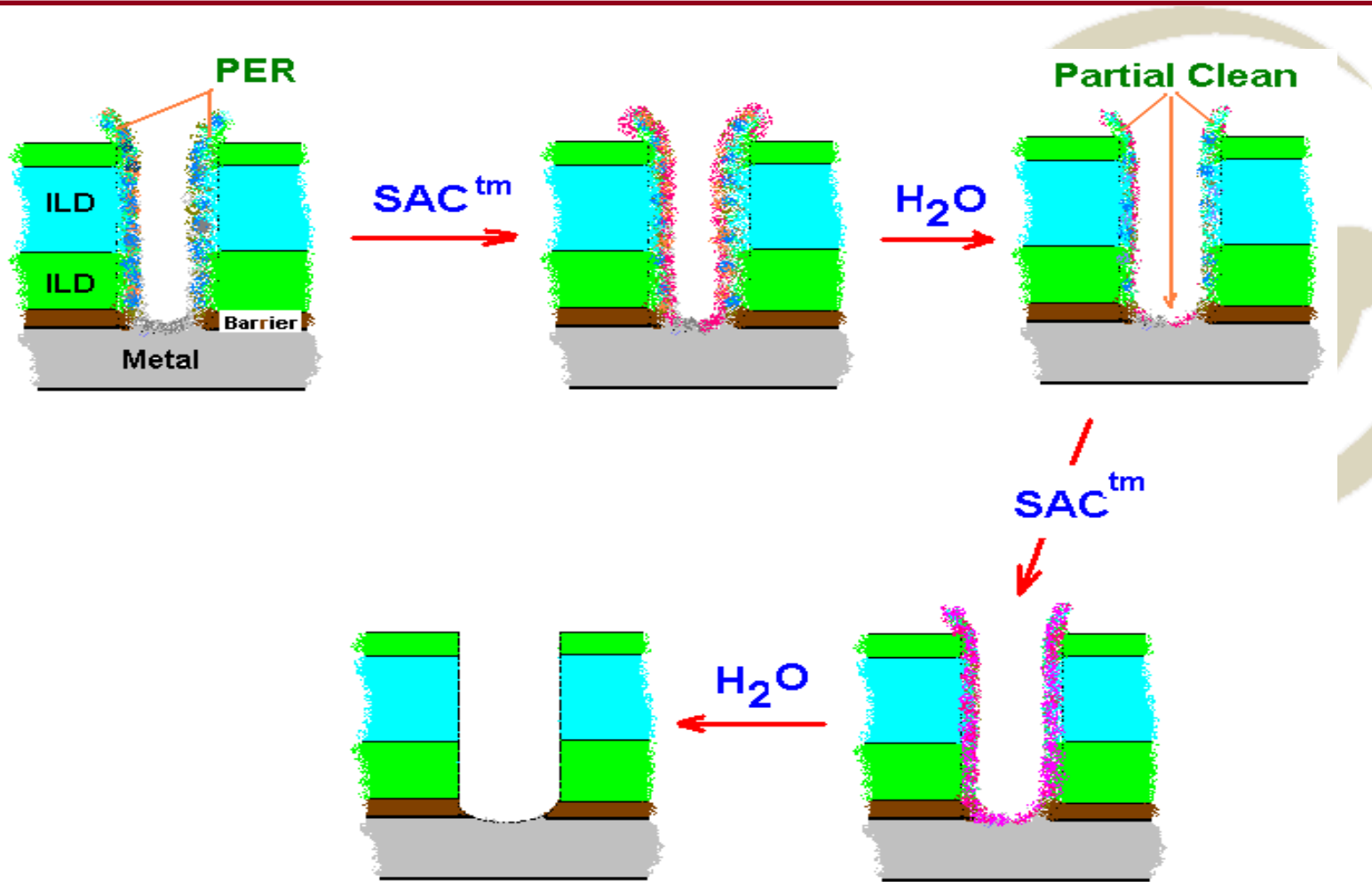
Proposed SAC™ Mechanism

Proposed Mechanism for SAC™ Chemistries



R. Small 6/11/01

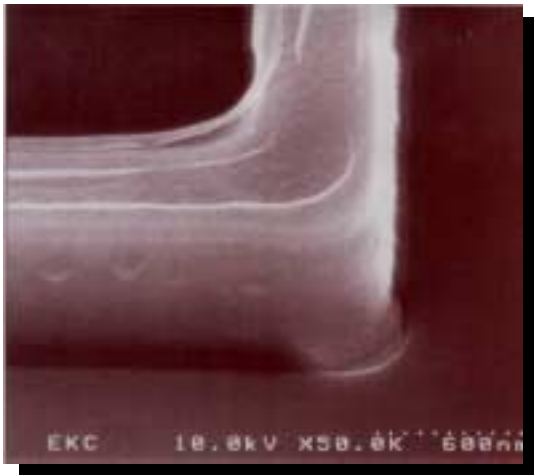
Via Cleaning Method for Single/Spray Tools



Tested with SEZ, FSI and SemiTool

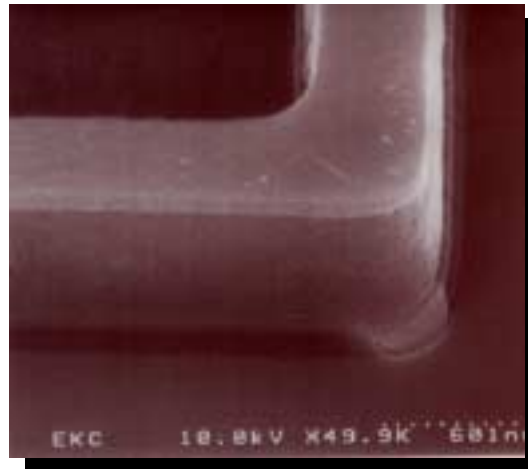
W Plug Compatibility in Unlanded Applications

After Etch



After EKC640™

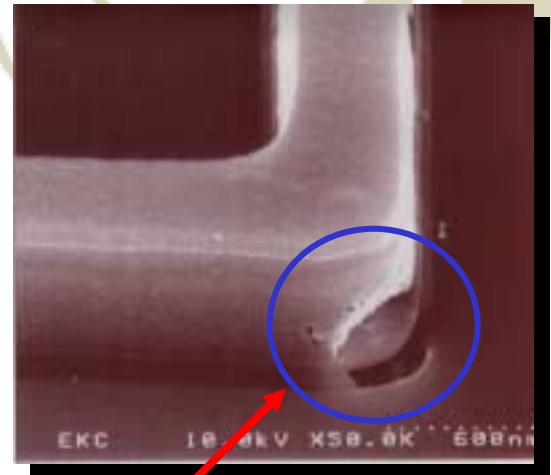
Temp.: Ambient
Time: 20 min.



Outstanding Clean Result

Failure Mode

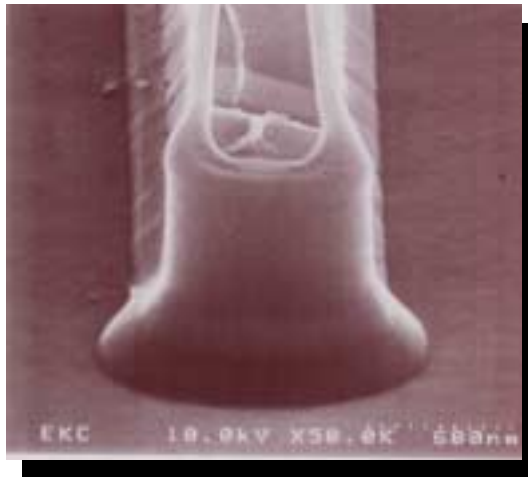
Conventional Remover
Temp.: 70° Time: 20 min.



W Plug eroded

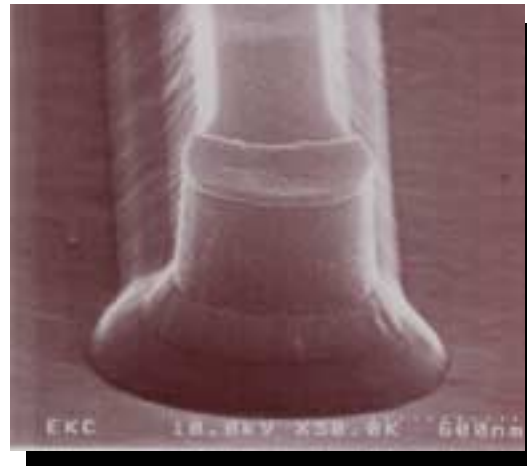
SAC™ EKC640™ Metal Cleaning Results

After Etch



After EKC640™

Temp.: Ambient
Time: 30 sec.



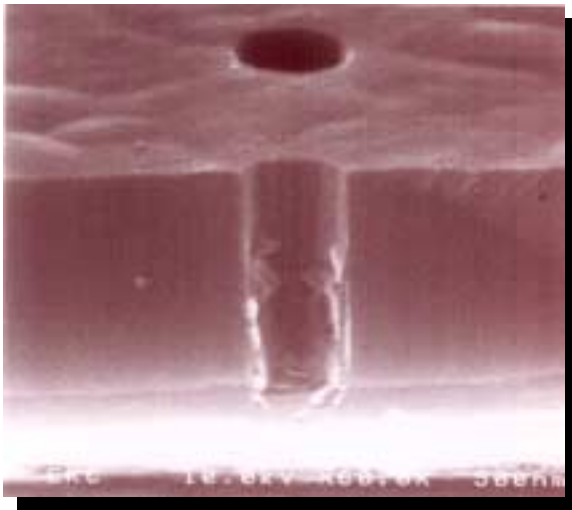
After EKC640™

Temp.: Ambient
Time: 5 min.

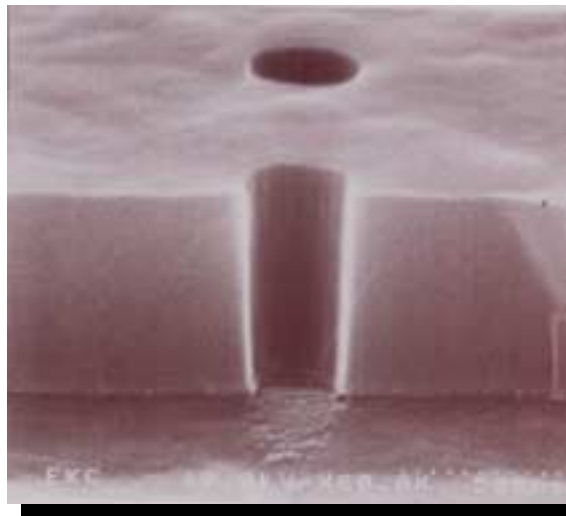


EKC640™ Via Cleaning Results

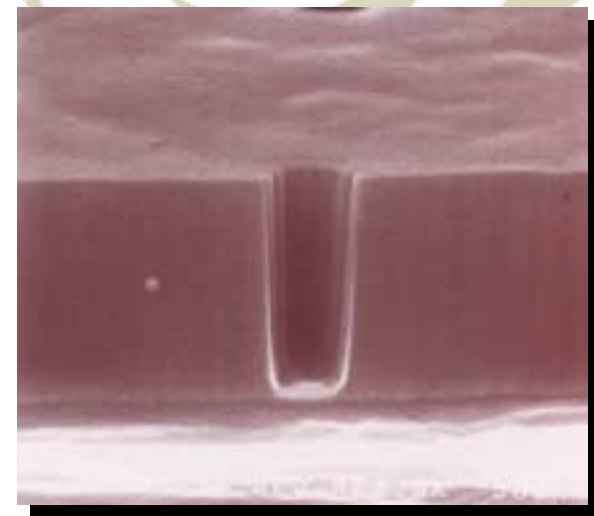
After Etch



After EKC640™
Temp.: Ambient
Time: 30 sec.

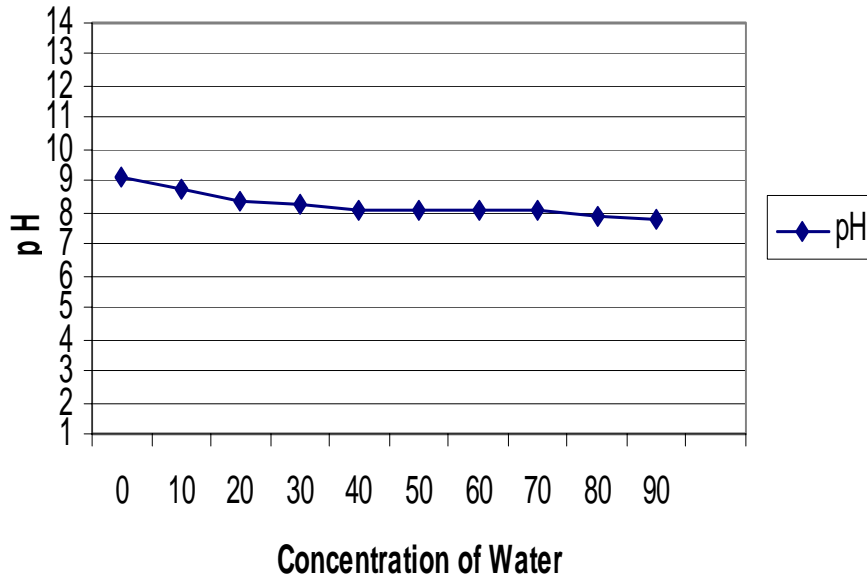


After EKC640™
Temp.: Ambient
Time: 5 min.

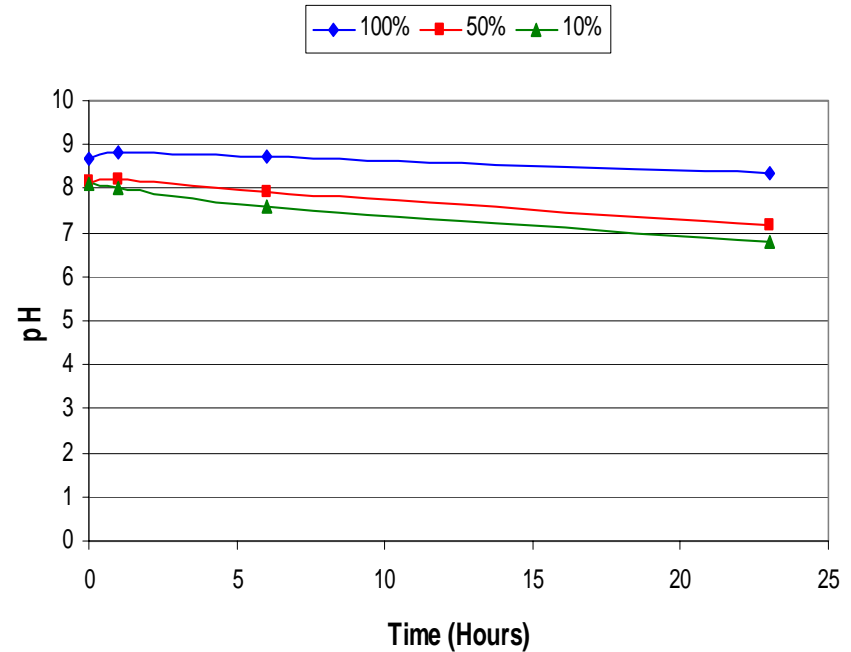


EKC640™ pH STUDY

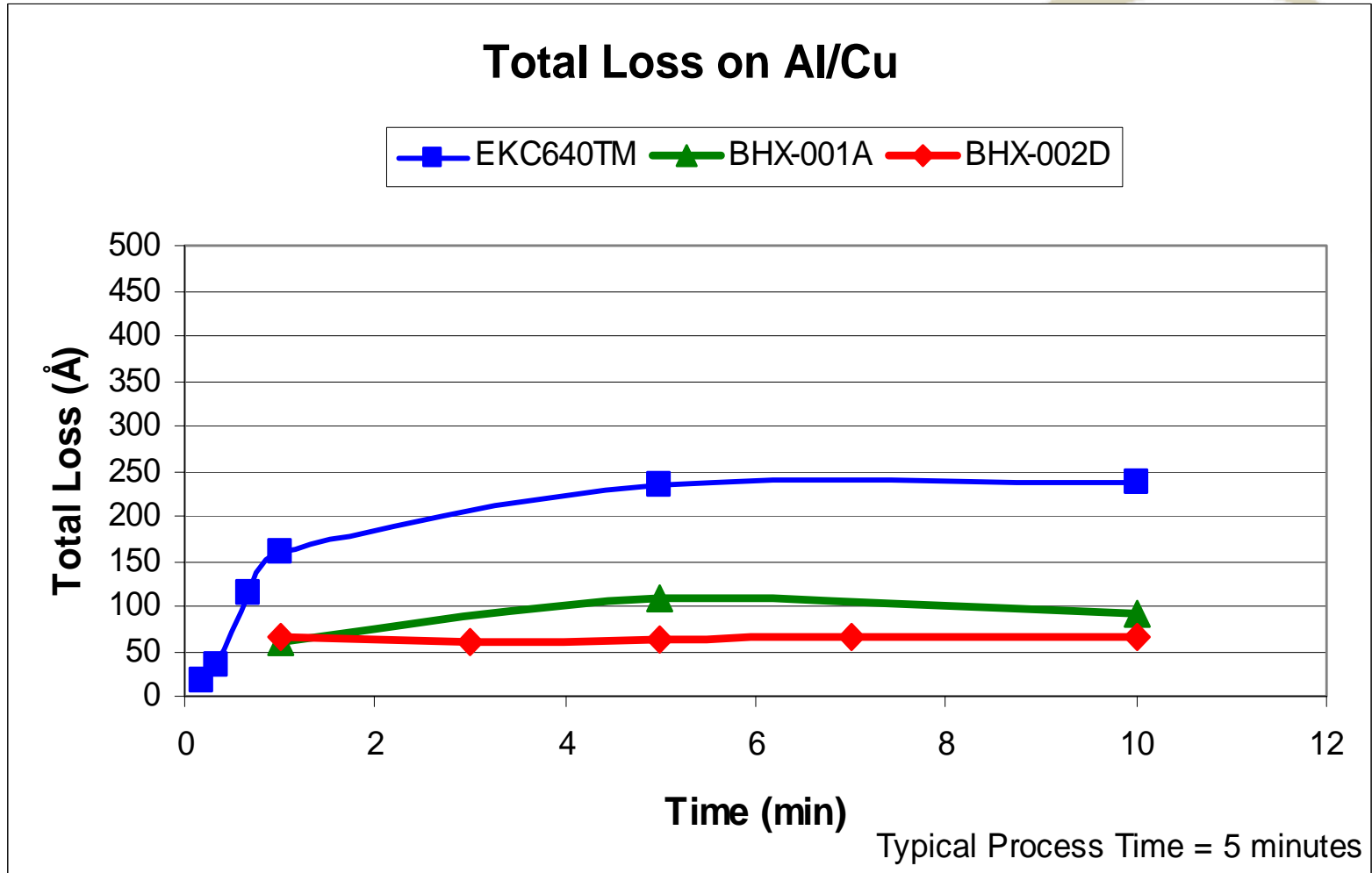
Effect of Water in EKC640(tm)



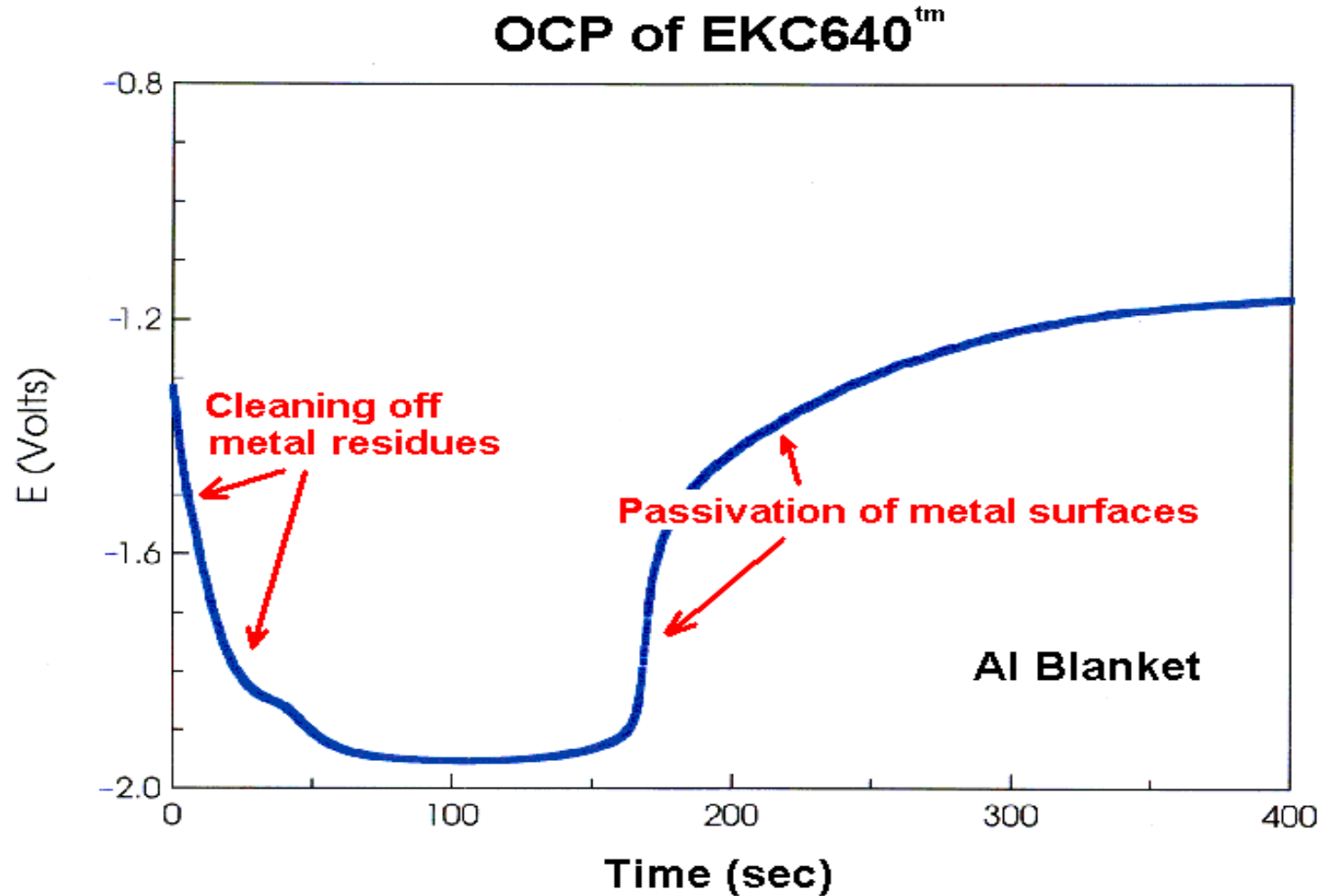
EKC640™ pH vs Time



Al/Cu Etch Rates: SAC™ Chemistries

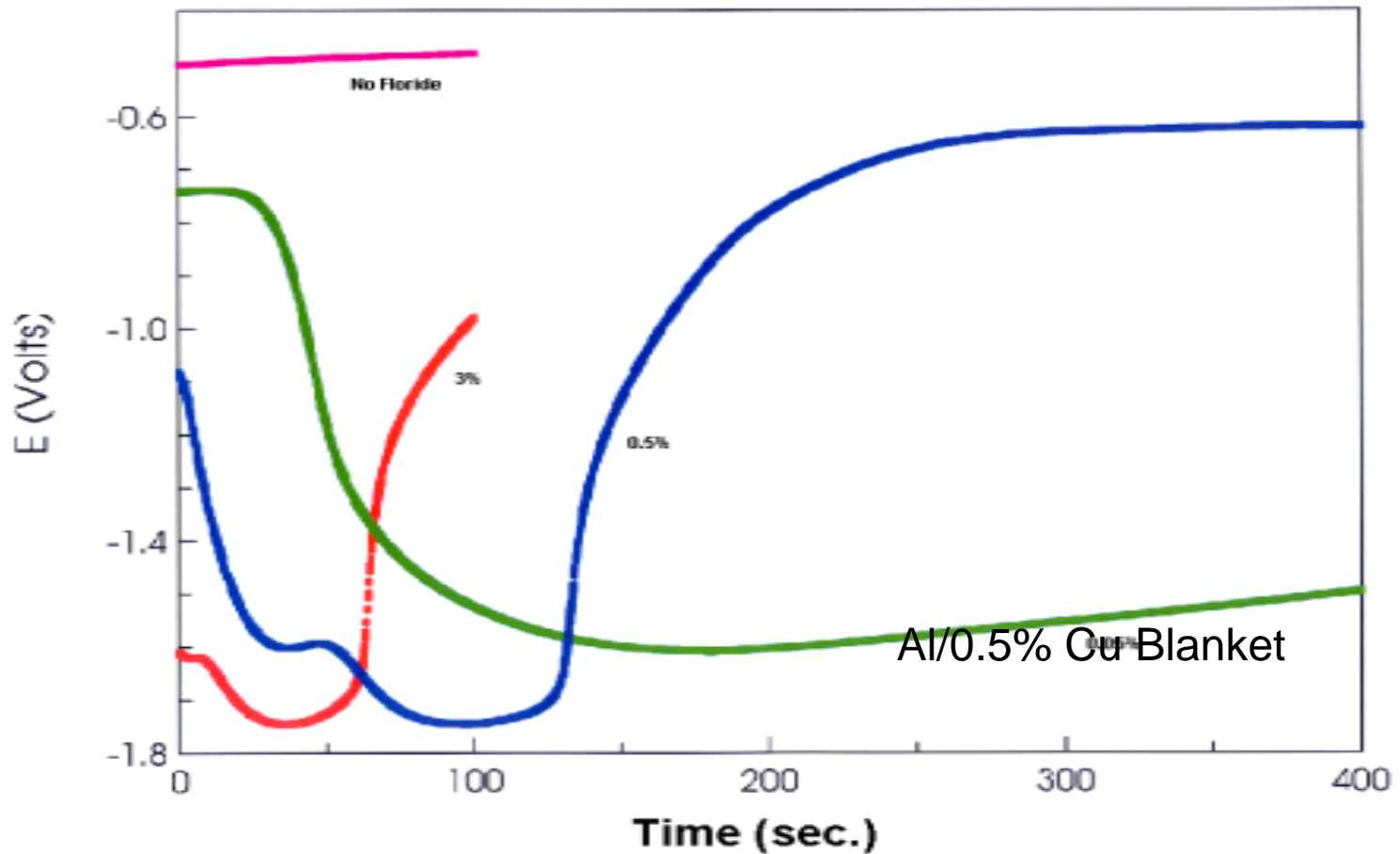


OCP of EKC640™



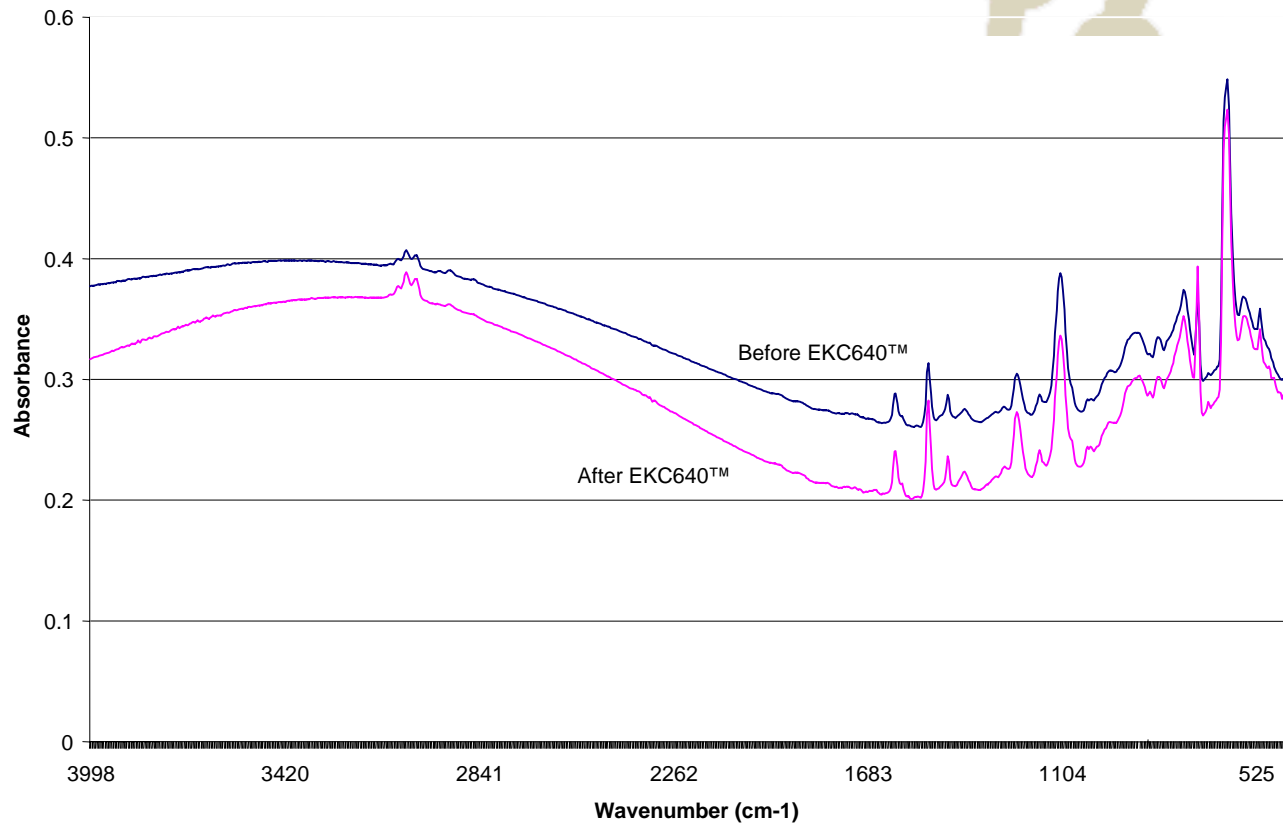
OCP vs Fluoride Concentration

OCP for a SAC™ Chemistry as a Function of Fluoride Concentration

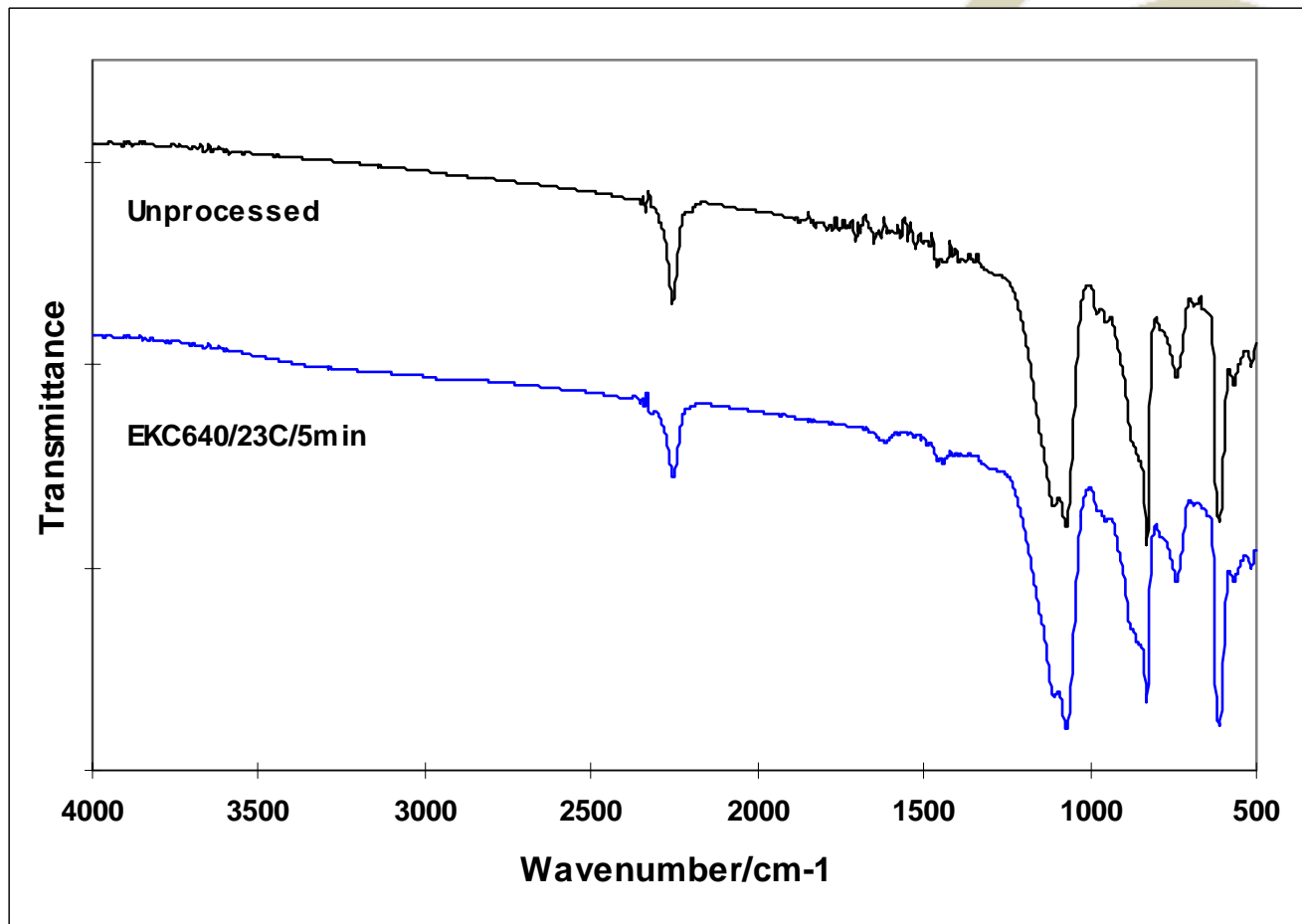


Compatibility with Low-k Dielectrics

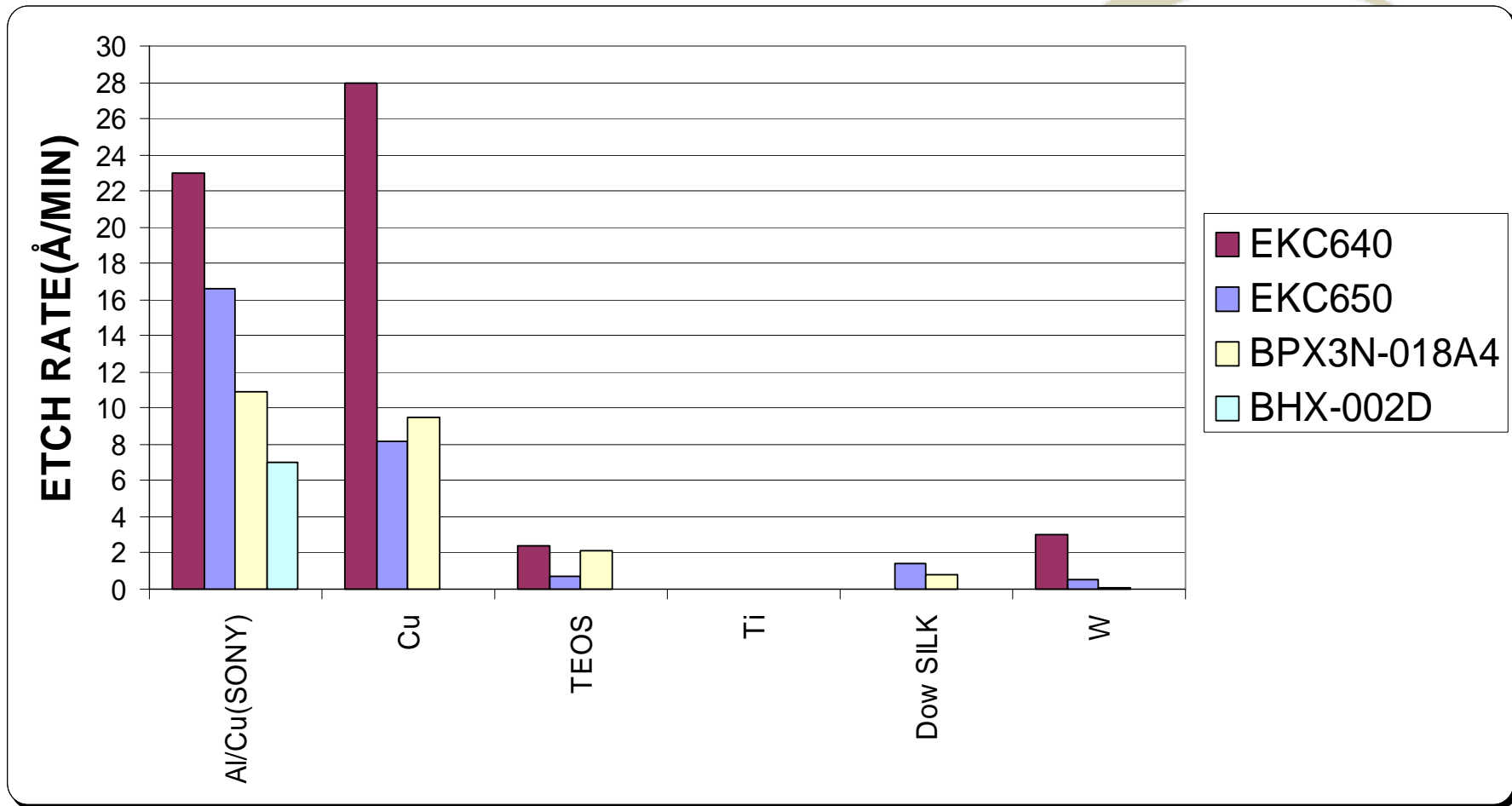
FT-IR Analysis of SiLK 450 Before and After Processing in EKC640™ for 5 Minutes at 23°C



EKC640™ Compatibility with FOx®



Etch Rate Data (SAC™ Chemistries)



Dynamic stirring at 25C

Blanket Wafer Etch Rates in Fluoride Chemistries

Film Type	EKC640™ (1)	BHX-002D (2)
	(Å/min)	(Å/min)
AlCu	8	3
Ti	< 0.1	< 0.1
W	< 0.1	< 0.1
Cu	0.1 - 6	0.1 - 3
TEOS	4	2 - 5
BPSG	2 - 4	2 - 5

(1) Testing was performed using a static bath.

(2) Testing was performed using a dynamic bath.

Operating conditions for tests conducted at ambient temperature for 30 minutes.

Note: Values may change with different substrates and process conditions. This information is intended as a relative guide only.

Blanket Wafer Etch Rates in Fluoride Chemistries

Film Type	EKC640™ (1)	BHX-002D (2)
	(Å/min)	(Å/min)
Silk	~ 0	~ 0
Flare	~ 0	~ 0
MSQ	+ 10	3 - 5
BCB	~ 0	T.B.D.
SPEEDFILM	5 - 7	N.D.
LPSZ - R	7	N.D.
HOSP	10	T.B.D.
Flare 2	0.4 - 2	T.B.D.
FOX	7-54	T.B.D.

(1) Testing was performed using a static bath.

(2) Testing was performed using a dynamic bath.

Operating conditions for tests conducted at ambient temperature for 30 minutes.

Note: Values may change with different substrates and process conditions. This information is intended as a relative guide only.

SAC™ Material Compatibility

Temperature: Ambient Room Temperature

Exposure Time: 5 days

*All of these
materials passed*

- Polypropylene
- PVDF
- PFA
- PVC
- Kalrez 1050LF; Kalrez 2037;
Kalrez 4079; Kalrez 8201
- PEEK
- Chemrez 550
- SEP21 treated 316 SS
- Electropolished 316 SS

SAC™ Design Criteria

- **Ability to remove post etch residues @ 20°C to 30°C** ✓
- **Process times: 1 to 25 minutes** ✓
- **Buffered semi-aqueous chemistries with stable pH** ✓
- **Designed for all types of cleaning equipment**
 - Spray tools: SEZ, FSI and SemiTool ✓
 - Wet benches: Akrion and others ✓
- **Low viscosity for equipment and filter capability** ✓
- **Ability to remove post etch residues without attacking the oxides** ✓
- **No W-Plug corrosion** ✓

SAC™ Design Criteria cont.

- **Compatible with most low-k dielectric materials** ✓
- **Ability to remove surface mobile ions** ✓
- **Does not absorb moisture during usage** ✓
- **Room temperature operation** ✓
- **Water rinseable (no intermediate rinse required)** ✓
- **Environmental friendly** ✓
- **Excellent bath life and loading create low Cost of Ownership (CoO)** ✓

General Conclusions

- **Cleaning effects depended on type and concentration of fluoride species and on the solvent system.**
 - Careful control of ionic activity can produce very specific cleaning chemistries (“silver bullets”).
 - Cleaning kinetics can be better matched to the equipment (wet benches, spray tools, single wafer tools).
 - Good performance on many structures with mild process conditions (Al/Cu, Ti, W, Cu).
 - Ability to remove surface mobile ions.
 - Low etch rates.
 - More options for rinsing (conserve DI water).